Fabrication of MoS₂ Photodetectors for Near-Infrared Biosensing Applications

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Over the last few decades, researchers have been developing novel and high-performance diagnostic biosensors using metallic nanoparticle-based localized surface plasmon resonance (LSPR) components.[1] In these biosensing devices, photodetectors with high photoresponsivity and low internal noise level are required to detect the optical signals induced by biomarker binding events (i.e., Antigen-antibody binding). In recent years, atomically thin (i.e., 2-25 nm thick) molybdenum disulfide (MoS₂) channels have been integrated with LSPR structures to enable fast and sensitive colorimetric monitoring of disease-related biomarkers.[2] However, such biosensors are mostly operated in the ultraviolet/visible wavelength regimes, which demands a purification step to separate out a variety of unwanted biological species that absorb visible lights. This process typically takes several hours, which prevent implementation of such sensors or immunoassay tools consistent with the whole blood assay with minimal sample preparation steps.[3] To meet this goal, a systematical study on high-performance near-infrared (NIR) photoconductors is strongly motivated because most biological species in the whole blood samples have high degrees of transparency for NIR lights.

In this work, we studied the photo-response properties (i.e., Photoresponsivity spectra) of inplane MoS_2 photodetectors as the function of their geometric dimensions (e.g., thickness, length, and width of photoactive layers) as well as fabrication conditions (e.g., doping, etching, and substrate choice). This work has enabled the NIR operation capabilities of plasmonic colorimetric biosensing, thereby reducing assay times and background interference.

Fig. 1(a) shows an as-fabricated MoS_2 photoconductor structure with effective channel length of ~1 µm laterally sandwiched by a pair of Ti/Au electrode pads, which secures a smooth, singlecrystal-domain sensing channel structure. The optimal MoS₂ channel thickness has been experimentally identified to be ~14 nm. To characterize optoelectronic properties of a MoS₂ photodetector, photocurrent is measured at fixed source-drain voltage, Vds = 1 V. Fig. 1(b) demonstrates the photoresponsivity spectra measured from a few-layer (FL) MoS₂ photodetector and a 14 nm thick multilayer MoS₂ photodetector. The 14 nm thick MoS₂ channel exhibits threefold higher photoresponsivity as compared to that of the few-layer MoS_2 channel (3 nm thick) within the NIR region. Up to the present time, the technological utility of multilayer MoS₂ has been underappreciated in comparison with monolayer and few-layer MoS₂. However, our study indicates that multilayer MoS₂ films exhibit the higher photoresponsivity and light absorption coefficients than those of monolayer films under NIR illumination, which is attributed to the screening effect of the thicker MoS₂ films for unwanted interference signals from the backgrounds and complex analyte fluids. Furthermore, root mean square (RMS) noise values were measured from 3-nm thick and optimized 14 nm thick pristine MoS₂ photodetectors and a 14 nm thick O₂ plasma-treated MoS₂ photodetector, as shown in Fig. 1(c). This comparison shows that the 15-nm thick MoS₂ channel exhibits 100-fold lower noise level than that of the 3 nm thick MoS₂ photoconductor and the O₂ plasma-treated 14 nm MoS₂ photodetector. This result can be attributed to the minimized substrate scattering effect in the larger thickness (10-20 nm) and smooth surface MoS₂ channel layers.

This work provides a guideline for making 2D-material-based NIR range photo-response devices implemented for the wash-free, mix-and-detection immunoassay of CEA in clinically relevant biofluids, including the whole blood.

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Fig. 1 MoS₂ photoconducting channels with different MoS₂ thicknesses: (a) Optical micrograph and AFM images showing the structure of a 15-nm thick MoS₂ channel with Ti/Au electrodes (Scale bar: 1 μ m). (b) Photoresponsivity spectrum of 15-nm thick and 3nm thick few-layer MoS₂ sensing channels. The photoresponsivity is given by R = Iph/P, where Iph is the photocurrent and P is the intensity of the incident light. (c) RMS noise values measured for pristine MoS₂ channels of 3 and 14 nm in thickness, and O₂ plasma-treated 14 nm thickness, respectively.